

# SG100N03P

100V N-Channel Power MOSFET

	TO-220AB	
$    V_{\text{DSS}} , 100V \\ R_{\text{DS(ON)}} , 27m\Omega \mbox{ (max.) } @ V_{\text{GS}} = 10V \\ R_{\text{DS(ON)}} , 28.5m\Omega \mbox{ (max.) } @ V_{\text{GS}} = 4.5V \\ I_D , 38A $	GDS	G

Description	Features
The SG100N03P uses advanced Trench technology and designs to provide excellent R <sub>DS(ON)</sub> with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul> <li>Low On-Resistance</li> <li>Low Input Capacitance</li> <li>Low Miller Charge</li> <li>Low Input / Output Leakage</li> <li>Pb-free lead plating; RoHS compliant</li> </ul>
	Applications
	<ul> <li>Motor / Body Load Control</li> <li>Automotive Systems</li> <li>Load Switch</li> <li>DC-DC converters and Off-line UPS</li> </ul>

## **Ordering Information**

Ordering Code	<b>RoHS Status</b>	Package	Package Code	Packing	Quantity
SG100N03P	Halogen-Free	TO-220AB	Р	Tube	50

### Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parame	ter	Symbol	Value	Unit
Drain-Source Voltage		VDS	100	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Current Continuous	T <sub>A</sub> =25°C	1	38	A
Drain Current-Continuous	T <sub>A</sub> =100°C	ID ID	24	A
Drain Current-Pulsed Note 1		IDM	39	A
Avalanche Current, L=0.1mH		I <sub>AS</sub>	24	A
Avalanche Energy, L=0.1mH		Eas	29	mJ
Maximum Davier Dissignation	T <sub>A</sub> =25°C	D-	83.9	W
Maximum Power Dissipation	T <sub>A</sub> =100°C	PD PD	33.6	W
Operating Junction Temperature Range		TJ	150	°C

# Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Thermal resistance, Junction-to-Ambient Note 2	Reja	Steady State	-	40.7		°C/W
Thermal resistance, Junction-to-Case Note 2	Rejc	Steady State	-	1.49		°C/W



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#### Electrical Characteristics (T\_=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BVDSS	V <sub>GS</sub> =0V, I <sub>DS</sub> =250µA	100	-	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage	lgss	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250µA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	Р	V <sub>GS</sub> =10V, I <sub>DS</sub> =20A	-	-	27	mΩ
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>DS</sub> =10A	-		28.5	

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss			1858	-	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, f=1MHz		113		pF
Reverse Transfer Capacitance	Crss		-	47	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>		-	9	-	
Rise Time	tr	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V,	-	7.8	-	
Turn-Off Delay Time	T <sub>d(off)</sub>	R <sub>G</sub> =3Ω, I <sub>D</sub> =10A	-	28.9	-	ns
Fall Time	tr		-	16	-	
Total Gate Charge at 10V	Qg		-	36.6	-	
Gate to Source Gate Charge	Qgs	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =10A	-	8.1	-	nC
Gate to Drain "Miller" Charge	Qgd		-	7.1	-	1

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =10A	-	-	1.3	V
Body Diode Reverse Recovery Time	trr		-	24.4	-	ns
Body Diode Reverse Recovery Charge	Qrr	l⊧=10A, dl/dt=500A/µs	-	107.5	-	nC
Reverse Recovery Current	IRRM	V <sub>DS</sub> =50V,I <sub>F</sub> =10A,di/dt=500A/µs		8.8		Α

Notes:

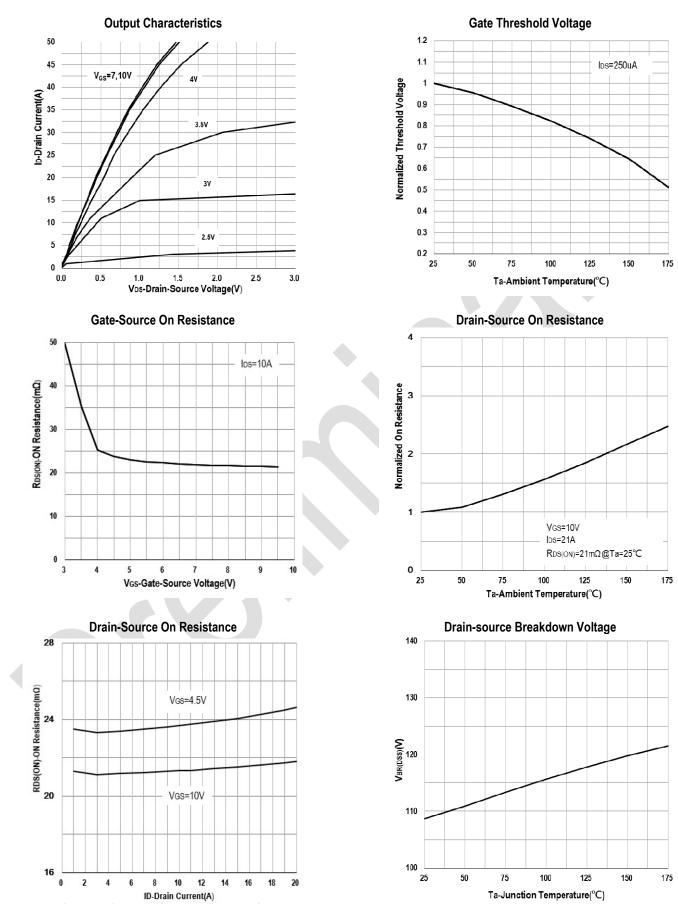
1. Pulse Test: Pulse Width  $\leq$  10ms, Duty Cycle  $\leq$  1%.

 R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BJA</sub> is determined by the user's board design. R<sub>BJA</sub> shown below for single device operation on FR-4 in still air.



# SG100N03P 100V N-Channel Power MOSFET

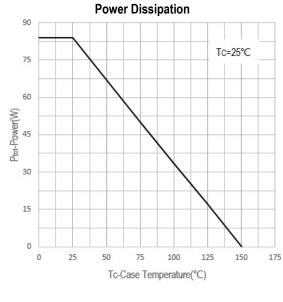
# **Typical Operating Characteristics**



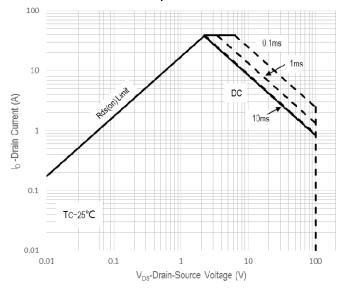


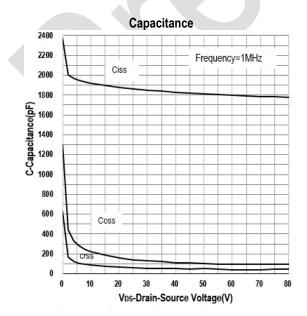
SG100N03P 100V N-Channel Power MOSFET

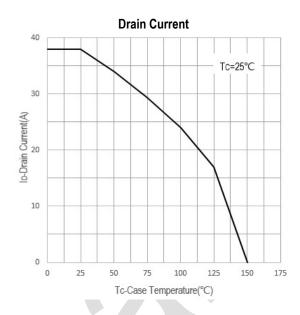
# **Typical Operating Characteristics (Cont.)**



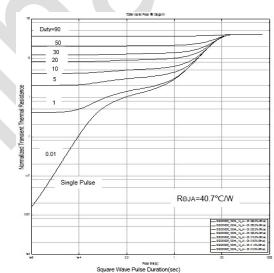
Safe Operation Area



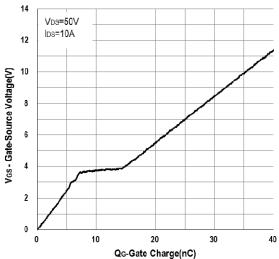




**Thermal Transient Impedance** 











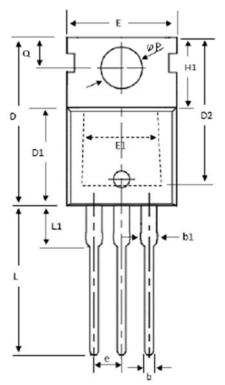
## **Marking Information**

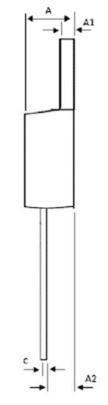
ТО-220АВ (Р)	Marking Rule
TO-220AB (P) Laser Marking SG100N03P YYMMXXX	Marking Rule         Line 1 : Device         SG100N03P         Line 2 : Date Code         YYMMXXX         YY : Year Code         MM : Month         XXX : Serial Number



# Package of Dimension

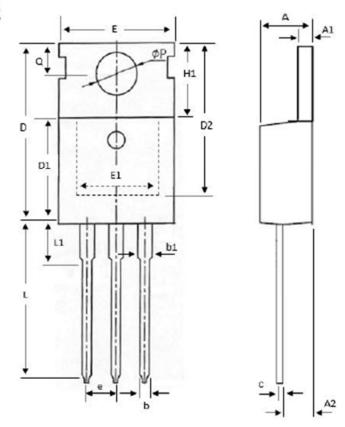
G-TYPE





Symbol	Min	Nor	Max
A	4.20	4.45	4.70
A1	1.15	1.28	1.40
A2	2.20	2.45	2.70
b	0.70	0.83	0.95
b1	1.15	1.45	1.75
С	0.40	0.50	0.60
D1	8.80	9.10	9.40
D2	11.75	-	-
E	9.70	10.03	10.36
E1	6.86	-	-
е		2.54 BSC	)
H1	6.25	6.55	6.85
L	12.75	13.38	14.00
L1	-	-	4.00
P	3.40	3.70	4.00
Q	2.60	2.80	3.00

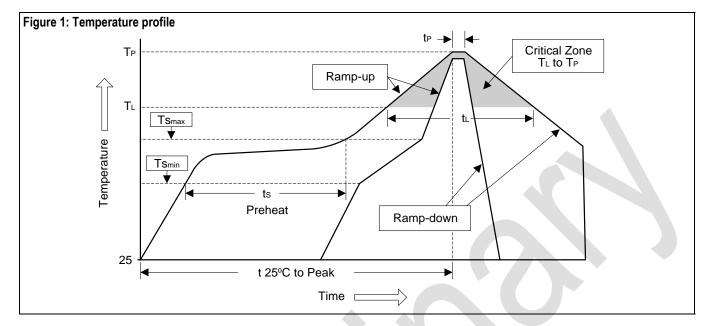
P-TYPE H-TYPE





#### **Soldering Methods for Silicongear's Products**

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (TL)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t <sub>P</sub> )		
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

#### 3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec





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